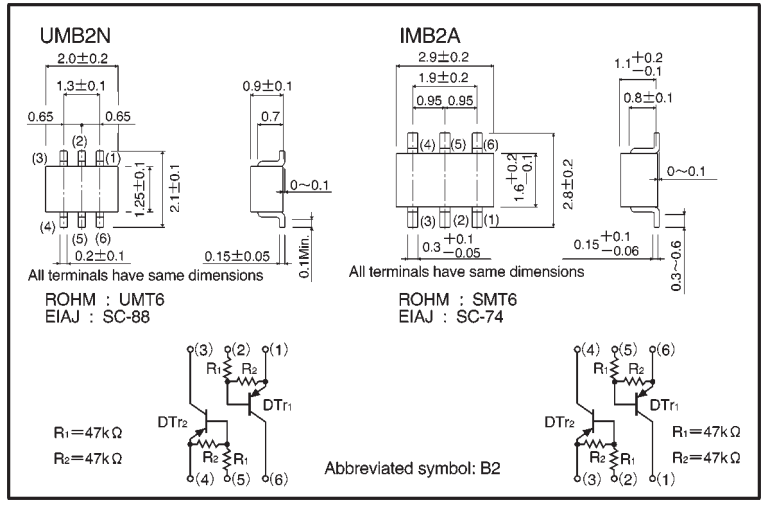
General purpose (dual digital transistors)

UMB2N / IMB2A

●Features

1) Two DTA144E chips in a UMT or SMT package.
2) Same size as UMT3 or SMT3 package, so same mounting machine can be used for both.
3) Transistor elements are independent, eliminating interference.

●External dimensions (Units: mm)



●Structure

Epitaxial planar type
PNP silicon transistor
(Built-in resistor type)

The following characteristics apply to both DTr_1 and DTr_2.

●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Supply voltage		V_{CC}	−50	V
Input voltage		V_I	−40	V
			10	
Output current		I_O	−30	mA
		$I_{C(Max.)}$	−100	
Power dissipation	UMB2N	Pd	150 (TOTAL)	mW ∗1
	IMB2A		300 (TOTAL)	mW ∗2
Junction temperature		Tj	150	℃
Storage temperature		Tstg	−55~+150	℃

∗1 120mW per element must not be exceeded.
∗2 200mW per element must not be exceeded.

(96-444-A144E)

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{I(off)}$	—	—	−0.5	V	V_{CC}=−5V, I_O=−100 μA
	$V_{I(on)}$	−3	—	—		V_O=−0.3V, I_O=−2mA
Output voltage	$V_{O(on)}$	—	−0.1	−0.3	V	I_O/I_I=−10mA/−0.5mA
Input current	I_I	—	—	−0.18	mA	V_I=−5V
Output current	$I_{O(off)}$	—	—	−0.5	μA	V_{CC}=−50V, V_I=0V
DC current gain	G_I	68	—	—	—	V_O=−5V, I_O=−5mA
Transition frequency	f_T	—	250	—	MHz	V_{CE}=−10mA, I_E=5mA, f=100MHz ＊
Input resistance	R_1	32.9	47	61.1	kΩ	—
Resistance ratio	R_2/R_1	0.8	1	1.2	—	—

＊ Transition frequency of the device

●Packaging specifications

	Packaging type	Taping	
	Code	TN	T110
Part No.	Basic ordering unit (pieces)	3000	3000
UMB2N		○	—
IMB2A		—	○

●Electrical characteristic curves

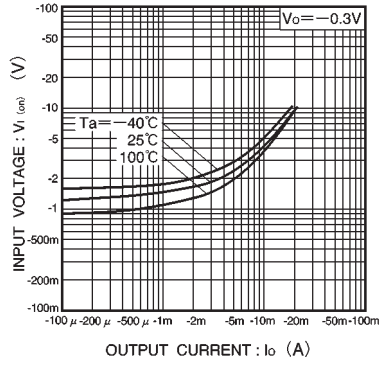


Fig.1 Input voltage vs. output current (ON characteristics)

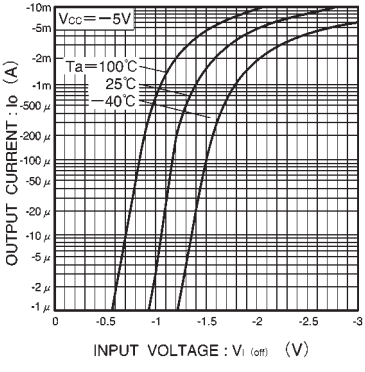


Fig.2 Output current vs. input voltage (OFF characteristics)

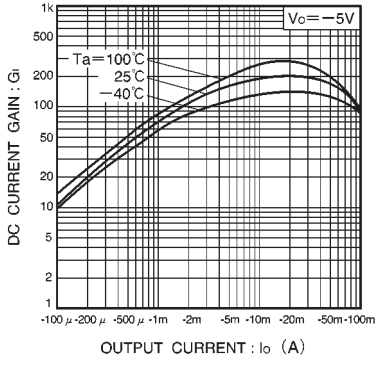


Fig.3 DC current gain vs. output current

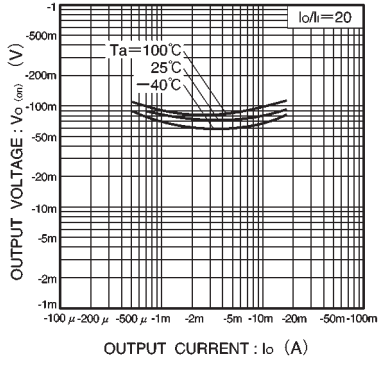


Fig.4 Output voltage vs. output current